ROITHNER LASERTECHNIK
Wiedner Hauptstraße 76, A-1040 Vienna, Austria
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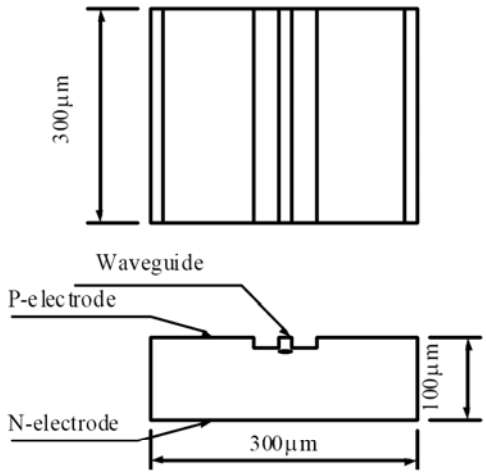
CHIP-980-P50

■Specifications

(1) Size : 300*300*100 μm
(2) Device: Laser diode bare chip
(3) Structure Double channel , single ridge waveguide

■External dimensions(Unit : μm)



P-electrode and N-electrode are both gold pad.
Channel depth : 1 ～ 1.5 μm

■Absolute Maximum Ratings(Tc=25℃)

Parameter	Symbol	Rating	Unit
Optical Output	Po	**50**	mW
Reverse Voltage	Vr	**2**	V
Operating Temperature	Top	-10～+40	℃
Storage Temperature	Tstg	-15～+85	℃

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■Electrical and Qptical Characteristics(Tc=25℃)

Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
Threshold Current		Ith	-	-	**12**	**20**	mA
Operating Current		Iop	Po=50mW	-	**75**	**85**	mA
Operating Voltage		Vop	-	**1**	**1.5**	**2.1**	Volt
Slope Efficiency		η	$\frac{30mW-10mW}{I_{30mW}-I_{10mW}}$	**0.65**	**0.8**	-	mW/mA
Beam Divergence (FWHM)	Parallel	θ //	Po=50mW	**8**	**13**	**18**	deg.
	Perpendicular	θ ⊥	Po=50mW	**25**	**30**	**35**	deg.
Lasing Wavelength		λ	Po=50mW	**970**	**980**	**995**	nm

◎ θ // and θ ⊥ are defined as the angle within which the intensity is 50% of the peak value.
◎Measuring Conditions : Pulse width=5μs , Duty cycle=1%

SPECIFICATIONS ARE SUBJECT TO CHANGE WITHOUT NOTICE.